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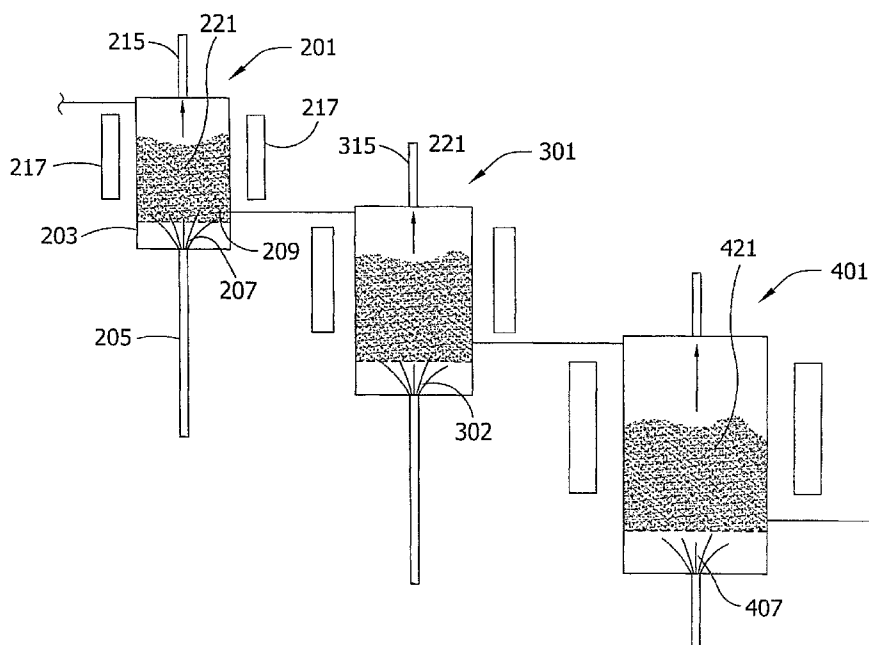
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(54) Title: HIGH PURITY GRANULAR SILICON AND METHOD OF MANUFACTURING THE SAME



(57) Abstract: A high-purity semiconductor grade granular silicon composition and methods for making the same are disclosed. Commercial quantities of the granular silicon can be produced by depositing silicon on silicon seeds in a first chemical vapor deposition (CVD) reactor, thereby growing the seeds into larger secondary seeds. Additional silicon is deposited on the secondary seeds in a second CVD reactor. Dust is reduced in a third reactor. The methods disclosed herein can be used to achieve higher throughput and better yield than conventional practices.

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